

LP3988-Q1 Micropower, 150-mA Ultra-Low-Dropout CMOS LDO With Power Good

1 Features

- Qualified for Automotive Applications
- AEC-Q100 Qualified With the Following Results:
 - Device Temperature Grade 1: -40°C to $+125^{\circ}\text{C}$ Ambient Operating Temperature
 - Device HBM ESD Classification Level H2
 - Device CDM ESD Classification Level C4B
- Operating Input Voltage 2.5 V to 6 V
- Power-Good Flag Output
- Logic-Controlled Enable
- Stable With Ceramic and High-Quality Tantalum Capacitors
- Fast Turnon
- Thermal Shutdown and Short-Circuit Current Limit
- 5-Pin SOT-23 Package

2 Applications

- Automotive
- CDMA Cellular Handsets
- Wideband CDMA Cellular Handsets
- GSM Cellular Handsets
- Portable Information Appliances

3 Description

The LP3988-Q1 is a 150-mA low-dropout regulator designed specially to meet requirements of portable battery applications. The LP3988-Q1 works with a space-saving 1- μF ceramic capacitor. The LP3988-Q1 features an error flag-output that indicates a faulty output condition.

The LP3988-Q1 has performance optimized for battery-powered systems to deliver low noise, extremely low dropout voltage, and low quiescent current. Regulator ground current increases only slightly in dropout, further prolonging the battery life.

Power-supply rejection is better than 60 dB at low frequencies and starts to roll off at 10 kHz. The device maintains high power-supply rejection down to lower input voltage levels common to battery-operated circuits.

The device is ideal for mobile phone and similar battery-powered wireless applications. It provides up to 150 mA, from a 2.5-V to 6-V input, consuming less than 1 μA in disable mode, and has fast turnon time less than 200 μs .

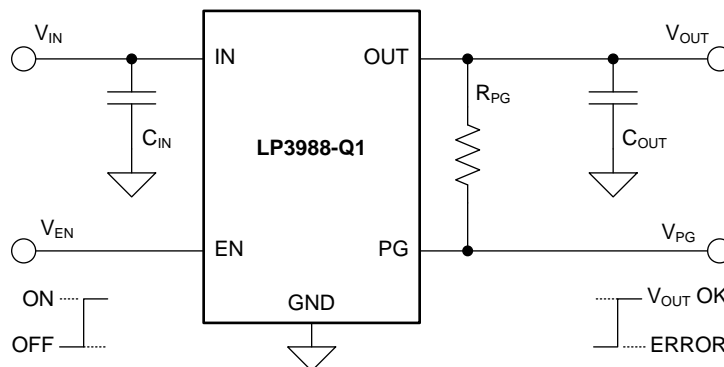
The LP3988-Q1 is available in a 5-pin SOT-23 package, has performance specified for the -40°C to $+125^{\circ}\text{C}$ temperature range, and is available in a 2.85-V output voltage. For other voltage options, contact TI sales.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
LP3988-Q1	SOT-23 (5)	2.90 mm x 1.60 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic



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4 Revision History

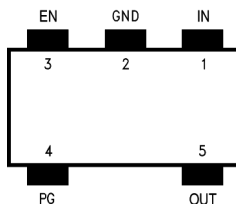
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (June 2013) to Revision B	Page
• Changed "Voltage Regulator" to "LDO" in title of data sheet	1
• Added <i>Device Information</i> and <i>Pin Configuration and Functions</i> sections, <i>ESD Ratings</i> table, <i>Feature Description</i> , <i>Device Functional Modes</i> , <i>Application and Implementation</i> , <i>Power Supply Recommendations</i> , <i>Layout</i> , <i>Device and Documentation Support</i> , and <i>Mechanical, Packaging, and Orderable Information</i> sections; changed pin names from VIN, VOUT and VEN to IN, OUT , and EN	1
• Changed Power dissipation from "364 mW" to "469 mW" in <i>Absolute Maxium Ratings</i> table note	4
• Changed R _{θJA} temp from "175°C/W" to "170.5°C/W" in <i>Absolute Maxium Ratings</i> table note	4
• Changed "4.5 mW" to "5.86 mW" in <i>Absolute Maxium Ratings</i> table note	4
• Added "High-K" after "Junction-to-ambient thermal resistance".....	4
• Updated <i>Thermal Information</i> values and added table note 2	4
• Added <i>Power Dissipation</i> and <i>Estimating Junction Temperature</i> sections	14

Changes from Original (March 2013) to Revision A	Page
• Deleted other voltages and left only 2.5 V	1
• Added TI sales note for additional voltages	1
• Changed θ _{JA} temp from 220°C/W to 175°C/W in <i>Absolute Maxium Ratings</i> table note	4
• Changed voltage in the title of the first two Typical Characteristics graphs (<i>Ripple Rejection Ratio</i>) from 2.6 to 2.85	6
• Changed LP3988Q to correct device name of LP3988-Q1.....	11

5 Pin Configuration and Functions

**DBV Package
5-Pin SOT-23
Top View**



Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
EN	3	Input	Enable input logic, enable high
GND	2	Ground	Common ground
IN	1	Input	Input voltage of the LDO
PG	4	Output	Power Good flag (output): open-drain output, connected to an external pullup resistor. Active low indicates an output voltage out of tolerance condition.
OUT	5	Output	Output voltage of the LDO

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾⁽²⁾

	MIN	MAX	UNIT
Voltage	-0.3	6.5	V
Power Good (OUT, EN)	-0.3	See ⁽³⁾	V
Junction temperature, T _J		150	°C
Power dissipation ⁽⁴⁾		469	mW
Storage temperature, T _{stg}	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to the potential at the GND pin.
- (3) The lesser of V_{IN} + 0.3 V or 6 V.
- (4) The *Absolute Maximum* power dissipation depends on the ambient temperature and can be calculated using the formula: P_D = (T_J – T_A) / R_{θJA}, where T_J is the junction temperature, T_A is the ambient temperature, and R_{θJA} is the junction-to-ambient thermal resistance. The 469-mW rating appearing under *Absolute Maximum Ratings* for the 5-pin SOT-23 package results from substituting the absolute-maximum junction temperature, 150°C, for T_J, 70°C for T_A, and 170.5°C/W for R_{θJA}. More power can be dissipated safely at ambient temperatures below 70°C. Less power can be dissipated safely at ambient temperatures above 70°C. The absolute-maximum power dissipation can be increased by 5.86 mW for each degree below 70°C, and it must be derated by 5.86 mW for each degree above 70°C.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD) Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000	V
	Charged-device model (CDM), per AEC Q100-011	±750	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

	MIN	NOM	MAX	UNIT
I _N ⁽²⁾	2.5		6	V
OUT, EN	0		V _{IN}	V
Junction temperature, T _J	-40		125	°C

- (1) All voltages are with respect to the potential at the GND pin.
- (2) The minimum V_{IN} is dependant on the device output option. For V_{OUT(NOM)} < 2.5 V, V_{IN(MIN)} equals 2.5 V. For V_{OUT(NOM)} ≥ 2.5 V, V_{IN(MIN)} equals V_{OUT(NOM)} + 200 mV.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		LP3988-Q1	UNIT
		DBV (SOT-23)	
		5 PINS	
R _{θJA} ⁽²⁾	Junction-to-ambient thermal resistance, High-K	170.5	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	124.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	30.9	°C/W
ψ _{JT}	Junction-to-top characterization parameter	17.6	°C/W
ψ _{JB}	Junction-to-board characterization parameter	30.4	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics*.
- (2) Thermal resistance value R_{θJA} is based on the EIA/JEDEC High-K printed circuit board defined by: *JESD51-7 - High Effective Thermal Conductivity Test Board for Leadless Surface Mount Packages*.

6.5 Electrical Characteristics

Unless otherwise specified: $V_{EN} = 1.8\text{ V}$, $V_{IN} = V_{OUT} + 0.5\text{ V}$, $C_{IN} = 1\text{ }\mu\text{F}$, $I_{OUT} = 1\text{ mA}$, $C_{OUT} = 1\text{ }\mu\text{F}$; typical values and limits are for $T_J = 25^\circ\text{C}$, and minimum and maximum values and limits apply over the entire junction temperature range for operation, -40°C to $+125^\circ\text{C}$.⁽¹⁾⁽²⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ΔV_{OUT}	Output voltage tolerance	$T_J = 25^\circ\text{C}$	-2		2	% of $V_{OUT(NOM)}$
			-3.5		3.5	
	Line regulation error	$V_{IN} = V_{OUT(NOM)} + 0.5\text{ V}$ to 6 V $T_J = 25^\circ\text{C}$	-0.15		0.15	%V
		$V_{IN} = V_{OUT(NOM)} + 0.5\text{ V}$ to 6 V	-0.2		0.2	
Load regulation error ⁽³⁾	$I_{OUT} = 1\text{ mA}$ to 150 mA , $T_J = 25^\circ\text{C}$			0.005	%mA	
	$I_{OUT} = 1\text{ mA}$ to 150 mA			0.007		
PSRR	Power supply rejection ratio	$V_{IN} = V_{OUT(NOM)} + 1\text{ V}$, $f = 1\text{ kHz}$, $I_{OUT} = 50\text{ mA}$ (See Figure 15)		65		dB
		$V_{IN} = V_{OUT(NOM)} + 1\text{ V}$, $f = 10\text{ kHz}$, $I_{OUT} = 50\text{ mA}$ (See Figure 15)		45		
I_Q	Quiescent current	$V_{EN} = 1.4\text{ V}$, $I_{OUT} = 0\text{ mA}$, $T_J = 25^\circ\text{C}$		85	120	μA
		$V_{EN} = 1.4\text{ V}$, $I_{OUT} = 0$ to 150 mA		140	200	
		$V_{EN} = 0.4\text{ V}$		0.003	1	
V_{DO}	Dropout voltage ⁽⁴⁾	$I_{OUT} = 1\text{ mA}$		1	5	mV
		$I_{OUT} = 150\text{ mA}$, $T_J = 25^\circ\text{C}$		80	115	
		$I_{OUT} = 150\text{ mA}$			150	
I_{SC}	Short-circuit current limit	See ⁽⁵⁾		600		mA
e_n	Output noise voltage	BW = 10 Hz to 100 kHz , $C_{OUT} = 1\text{ }\mu\text{F}$		220		μV_{RMS}
C_{OUT}	Output capacitor	Capacitance ⁽⁶⁾	1		20	μF
		ESR ⁽⁶⁾	5		500	m Ω
TSD	Thermal shutdown temperature			160		$^\circ\text{C}$
	Thermal shutdown hysteresis			20		
ENABLE CONTROL CHARACTERISTICS						
I_{EN}	Maximum input current at EN	$V_{EN} = 0\text{ V}$ and $V_{IN} = 6\text{ V}$			0.1	μA
V_{IL}	Logic low input threshold	$V_{IN} = 2.5\text{ V}$ to 6 V			0.5	V
V_{IH}	Logic high input threshold	$V_{IN} = 2.5\text{ V}$ to 6 V	1.2			V

(1) All electrical characteristics having room-temperature limits are tested during production with $T_J = 25^\circ\text{C}$ or correlated using statistical quality control (SQC) methods. All hot and cold limits are specified by correlating the electrical characteristics to process and temperature variations and applying statistical process control.

(2) The target output voltage, which is labeled $V_{OUT(NOM)}$, is the desired voltage option.

(3) An increase in the load current results in a slight decrease in the output voltage and vice versa.

(4) Dropout voltage is the input-to-output voltage difference at which the output voltage is 100 mV below its nominal value.

(5) Short-circuit current is measured on input supply line after pulling down V_{OUT} to $95\% V_{OUT(NOM)}$.

(6) Specified by design. Not production tested. The capacitor tolerance should be $\pm 30\%$ or better over the full temperature range. The full range of operating conditions such as temperature, DC bias and even capacitor case size for the capacitor in the application must be considered during device selection to ensure this minimum capacitance specification is met. TI recommends X7R capacitor types to meet the full device temperature range.

Electrical Characteristics (continued)

Unless otherwise specified: $V_{EN} = 1.8\text{ V}$, $V_{IN} = V_{OUT} + 0.5\text{ V}$, $C_{IN} = 1\text{ }\mu\text{F}$, $I_{OUT} = 1\text{ mA}$, $C_{OUT} = 1\text{ }\mu\text{F}$; typical values and limits are for $T_J = 25^\circ\text{C}$, and minimum and maximum values and limits apply over the entire junction temperature range for operation, -40°C to $+125^\circ\text{C}$.⁽¹⁾⁽²⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER GOOD						
V_{THL}	PG low threshold	% of V_{OUT} (PG ON), $T_J = 25^\circ\text{C}$ ⁽⁷⁾	90%	93%	95%	
V_{THH}	PG high threshold	% of V_{OUT} (PG OFF), $T_J = 25^\circ\text{C}$ ⁽⁷⁾	92%	95%	98%	
V_{OL}	PG output logic low voltage	$I_{PULLUP} = 100\text{ }\mu\text{A}$, fault condition		0.02	0.1	V
I_{PGL}	PG output leakage current	PG off, $V_{PG} = 6\text{ V}$		0.02		μA

(7) The low and high thresholds are generated together. Typically a 2.6% difference is seen between these thresholds.

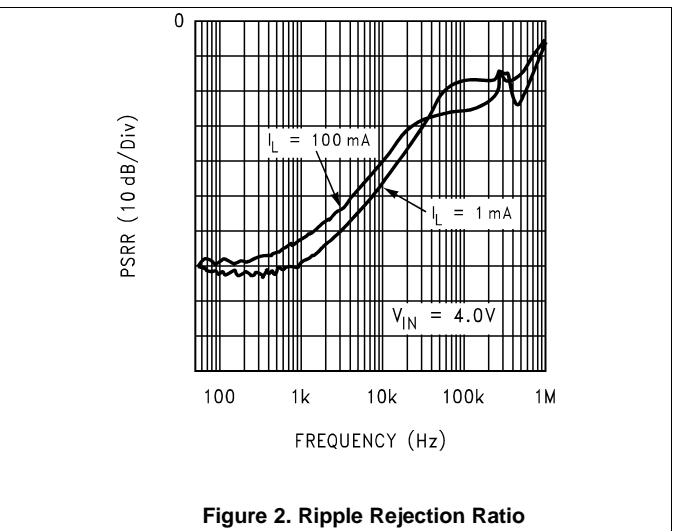
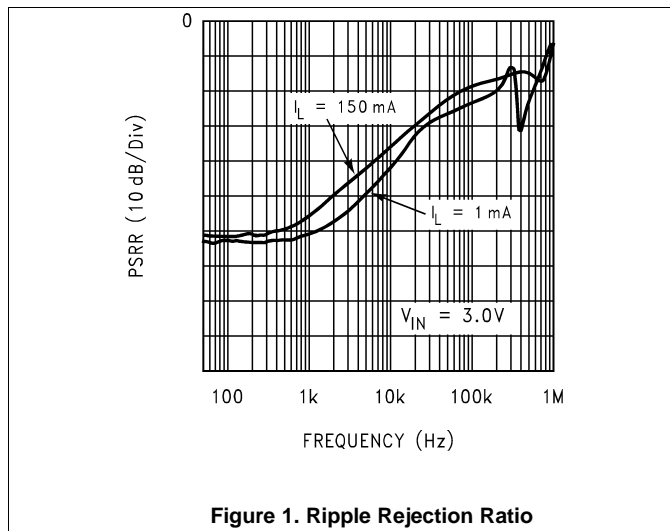
6.6 Timing Requirements

		MIN	NOM	MAX	UNIT
T_{ON}	PG turnon time ⁽¹⁾ , $V_{IN} = 4.2\text{ V}$		10		μs
T_{OFF}	PG turnoff time ⁽¹⁾ , $V_{IN} = 4.2\text{ V}$		10		μs

(1) Turnon time is time measured between the enable input just exceeding V_{IH} and the output voltage just reaching 95% of its nominal value.

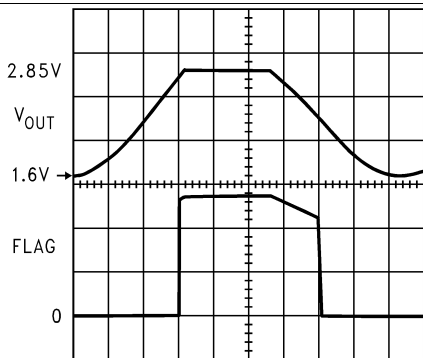
6.7 Typical Characteristics

Unless otherwise specified, $C_{IN} = C_{OUT} = 1\text{-}\mu\text{F}$ ceramic, $V_{IN} = V_{OUT} + 0.2\text{ V}$, $T_A = 25^\circ\text{C}$, EN pin is tied to V_{IN} .



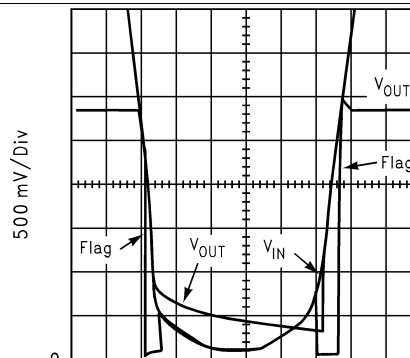
Typical Characteristics (continued)

Unless otherwise specified, $C_{IN} = C_{OUT} = 1\text{-}\mu\text{F}$ ceramic, $V_{IN} = V_{OUT} + 0.2\text{ V}$, $T_A = 25^\circ\text{C}$, EN pin is tied to V_{IN} .



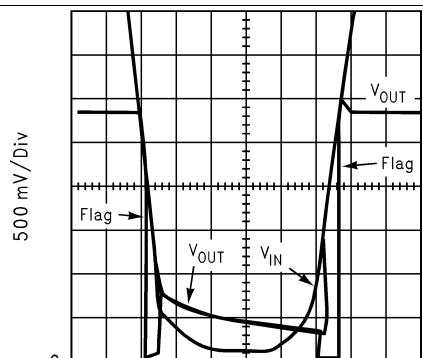
TIME (2 ms/Div)
FLAG pin pulled to V_{OUT} through a 100-k Ω resistor

Figure 3. Power-Good Response Time



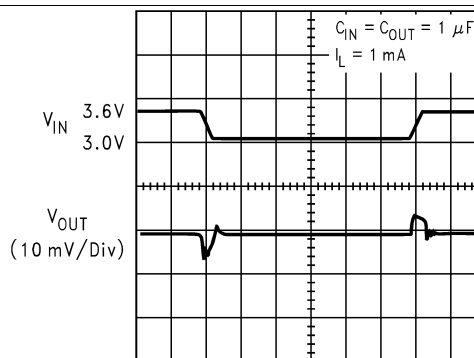
TIME (500 $\mu\text{s/Div}$)
FLAG pin pulled to V_{IN} through a 100-k Ω resistor

Figure 4. Power-Good Response Time



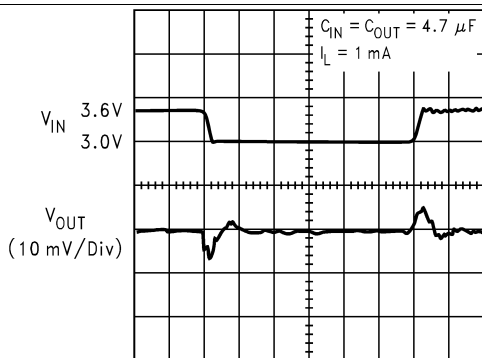
TIME (500 $\mu\text{s/Div}$)
FLAG pin pulled to V_{OUT} through a 100-k Ω resistor

Figure 5. Power-Good Response Time



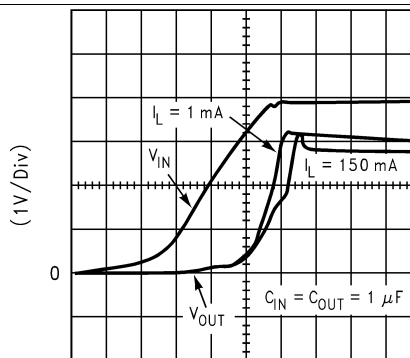
TIME (100 $\mu\text{s/Div}$)

Figure 6. Line Transient Response



TIME (100 $\mu\text{s/Div}$)

Figure 7. Line Transient Response



TIME (20 $\mu\text{s/Div}$)

Figure 8. Power-Up Response

Typical Characteristics (continued)

Unless otherwise specified, $C_{IN} = C_{OUT} = 1\text{-}\mu\text{F}$ ceramic, $V_{IN} = V_{OUT} + 0.2\text{ V}$, $T_A = 25^\circ\text{C}$, EN pin is tied to V_{IN} .

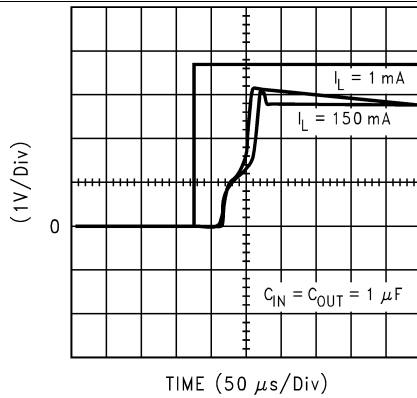


Figure 9. Enable Response

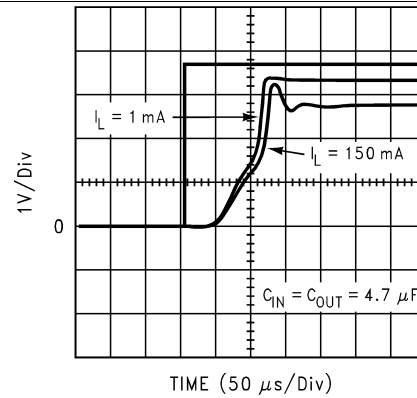


Figure 10. Enable Response

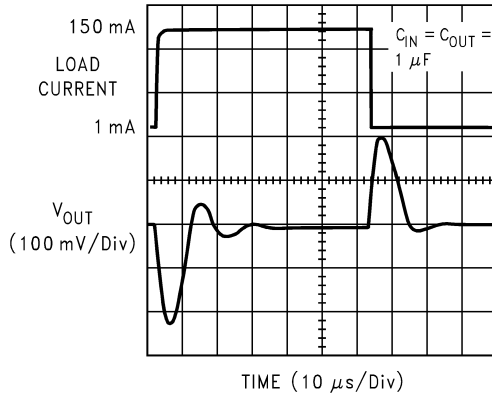


Figure 11. Load Transient Response

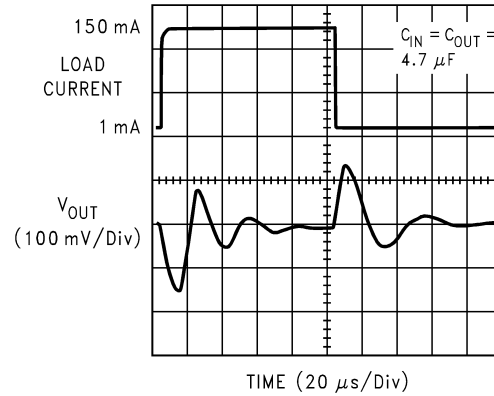


Figure 12. Load Transient Response

7 Parameter Measurement Information

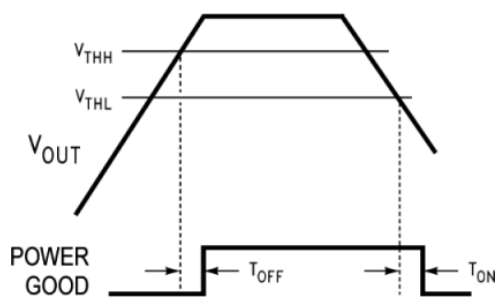


Figure 13. Power-Good Flag Timing

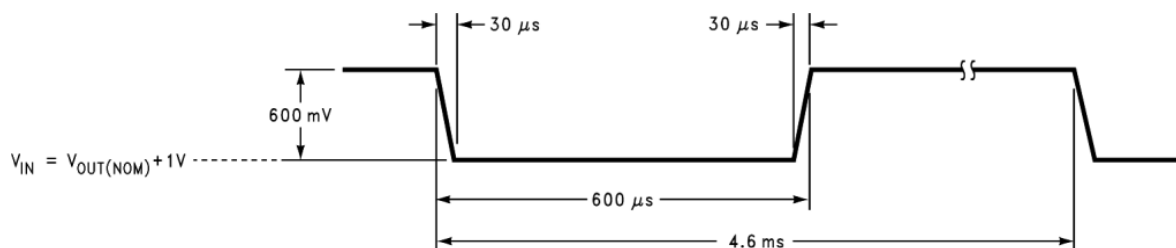


Figure 14. Line Transient Response Input Perturbation

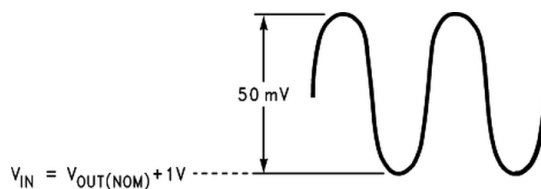


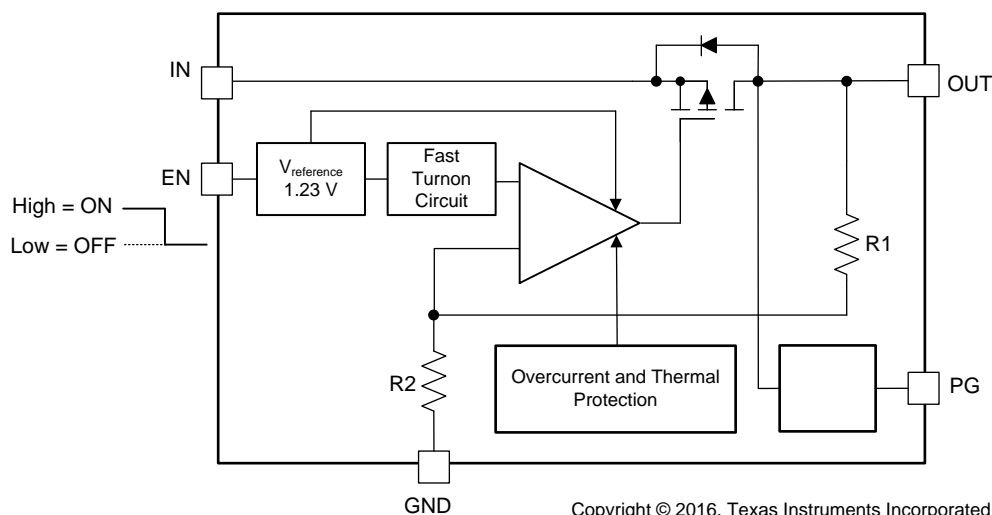
Figure 15. PSRR Input Perturbation

8 Detailed Description

8.1 Overview

The LP3988-Q1 is a combination of a low-dropout linear regulator with an enable function, along with a Power Good (PG) output. The enable function allows the LP3988-Q1 output to be selectively enabled, or disabled, as needed. The PG output goes high when the LP3988-Q1 output voltage is typically above 95% of nominal.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Enable (En)

A high input on the EN pin ($V_{EN} \geq V_{IH}$) activates the device, which turns the regulator to an ON state. A low input on the EN pin ($V_{EN} \leq V_{IL}$) disables the device which turns the regulator to an OFF state. Operating with V_{EN} between the V_{IL} and the V_{IH} thresholds is not recommended as the device status cannot be assured. For self-bias applications where the V_{EN} function is not needed, connect the EN pin to the IN pin.

8.3.2 Regulated Output (OUT)

The OUT pin is the regulated output voltage based on the internally pre-programmed voltage. The output has current limitation. In the event that the regulator drops out of regulation due to low input voltage, the output tracks the input minus a drop based on the load current. There is no UVLO circuitry. Device behavior is undefined when V_{IN} is below the minimum operating input voltage of either 2.5 V, or $V_{OUT} + 200$ mV, whichever is greater.

8.3.3 Power Good (PG) Output

The PG pin is an open-drain output and can be pulled up to any 6 V, or lower rail through an external pullup resistor. The PG pin is high-impedance when V_{OUT} is greater than the PG trip high threshold (V_{THH}). If V_{OUT} is less than the PG trip low threshold (V_{THL}), the open-drain output turns on and pulls the PG output low. If output voltage monitoring is not needed, the PG pin can be left floating or connected to GND. The behavior of the Power-Good feature is not ensured when V_{IN} is less than 2.5 V.

8.3.4 PG Delay Time

The Power-Good delay times (t_{ON} , t_{OFF}) are defined as the time period from when V_{OUT} crosses either the PG high trip threshold voltage (V_{THH}), or the PG low trip threshold voltage (V_{THL}), to when the PG output changes to the appropriate state. The power-good delay times are set internally, and both are typically 10 μ s. There is no external adjustment available to alter the delay times.

Feature Description (continued)

8.3.5 Current Limit

The fixed current limit (I_{SC}) of the LP3988-Q1 helps protect the regulator during output fault conditions. The maximum amount of current the device can source is typically 600 mA and is largely independent of input and output voltage. For reliable operation, do not operate the device in current limit for extended periods of time. Depending on power dissipation, thermal resistance, and ambient temperature, operating at the current limit may activate the thermal shutdown circuitry.

8.3.6 Thermal Shutdown (T_{SD})

Thermal shutdown (T_{SD}) protection disables the output when the junction temperature rises to approximately 160°C. This shutdown causes the device dissipation to go to zero, which allows the device to cool. When the device junction temperature cools to approximately 140°C, the output circuitry is automatically enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle ON and OFF. This cycling limits the dissipation of the regulator, protecting it from damage as a result of overheating. The thermal shutdown circuitry of the LP3988-Q1 has been designed to protect against temporary thermal overload conditions. The T_{SD} circuitry was not intended to replace proper heat sinking. Continuously running the LP3988-Q1 device in T_{SD} may degrade device reliability and lifetime.

8.3.7 Fast Turnon Time

The LP3988-Q1 utilizes a speed-up circuit to ramp up the internal V_{REF} voltage to its final value to achieve a fast output turnon time.

8.4 Device Functional Modes

8.4.1 Normal Operation

The device regulates to the nominal output voltage under the following conditions:

- The input voltage (V_{IN}) is at least either 2.5 V, or $V_{OUT} + 200$ mV, whichever is greater.
- The enable voltage (V_{EN}) is at least 1.2 V (V_{IH}).
- The output current is no more than the maximum rated current of 150 mA.
- The device junction temperature (T_J) is no more than the maximum specified operating junction temperature.

8.4.2 Dropout Operation

If the input voltage is lower than the nominal output voltage plus the specified dropout voltage (V_{DO}), but all other conditions are met for normal operation, the device operates in dropout mode. In this mode of operation, the output voltage is the same as the input voltage minus the dropout voltage. The transient performance of the device is significantly degraded because the pass device (PMOS transistor), no longer controls the current through the LDO. Line or load transients while operating in dropout can result in large output voltage deviations.

8.4.3 On/Off Input Operation

The LP3988-Q1 is turned off by pulling the EN pin low, and turned on by pulling it high. If this feature is not used, the EN pin must be tied to V_{IN} to keep the regulator output on at all time. To assure proper operation, the signal source used to drive the EN input must be able to swing above and below the specified turnon/turnoff voltage thresholds listed in the [Electrical Characteristics](#) section under V_{IL} and V_{IH} .

8.4.4 Disabled

The device is disabled under the following conditions:

- V_{EN} is no more than 0.6 V (V_{IL}).
- T_J is greater than the thermal shutdown temperature.

9 Application and Implementation

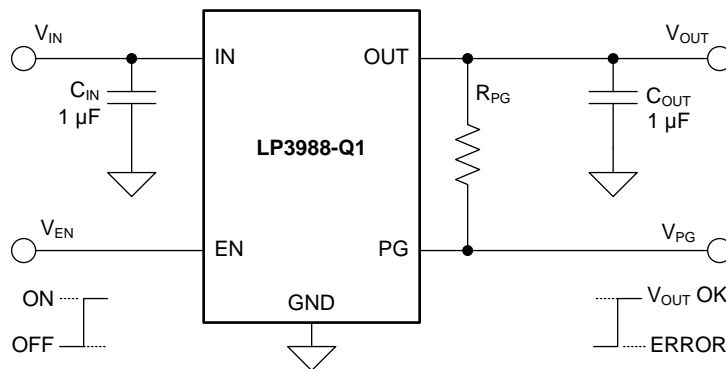
NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LP3988-Q1 voltage regulator offers the benefit of ultra-low-dropout voltage, low noise, very low standby current, and miniaturized surface-mount packaging. The LP3988-Q1 is designed for continuous, or sporadic (power back-up), battery-operated applications where very low standby current is critical to extending system battery life.

9.2 Typical Application



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Figure 16. LP3988-Q1 Typical Application

9.2.1 Design Requirements

For typical CMOS voltage regulator applications, use the parameters listed in [Table 1](#).

Table 1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Minimum input voltage	3.05 V
Output voltage	2.85 V
Output current	150 mA

9.2.2 Detailed Design Procedure

9.2.2.1 External Capacitors

Like any low-dropout regulator, the LP3988-Q1 requires external capacitors for regulator stability. The LP3988-Q1 is specifically designed for portable applications requiring minimum board space and smallest components. These capacitors must be correctly selected for good performance.

9.2.2.2 Input Capacitor

An input capacitance of at least 1 μF is required between the LP3988-Q1 IN pin and ground (the amount of the capacitance may be increased without limit). This capacitor must be located a distance of not more than 1cm from the input pin and returned to a clean analog ground. Any good quality ceramic, tantalum, or film capacitor may be used at the input

NOTE

Tantalum capacitors can suffer catastrophic failures due to surge current when connected to a low-impedance source of power (like a battery or a very large capacitor). If a tantalum capacitor is used at the input, it must be ensured by the manufacturer to have a surge current rating sufficient for the application.

There are no requirements for the equivalent series resistance (ESR) on the input capacitor, but tolerance and temperature coefficient must be considered when selecting the capacitor to ensure the capacitance is at least 1 μF over the entire operating temperature range.

9.2.2.3 Output Capacitors

The LP3988-Q1 is designed specifically to work with very small ceramic output capacitors. A ceramic capacitor (dielectric types Z5U, Y5V or X7R) in the 1- μF to 22- μF range with a 5-m Ω to 500-m Ω ESR range is suitable in the LP3988-Q1 application circuit.

It may also be possible to use tantalum or film capacitors at the output, but these are not as attractive for reasons of size and cost (see [Capacitor Characteristics](#)).

The output capacitor must meet the requirement for minimum amount of capacitance and also have an ESR value which is within a stable range (5 m Ω to 500 m Ω).

9.2.2.4 No-Load Stability

The LP3988-Q1 remains stable and in regulation with no external load. This is specially important in CMOS RAM keep-alive applications.

9.2.2.5 Capacitor Characteristics

The LP3988-Q1 is designed to work with ceramic capacitors on the output to take advantage of the benefits they offer: for capacitance values in the range of 1 μF to 4.7 μF , ceramic capacitors are the smallest, least expensive and have the lowest ESR values (which makes them best for eliminating high-frequency noise). The ESR of a typical 1- μF ceramic capacitor is in the range of 20 m Ω to 40 m Ω , which easily meets the ESR requirement for stability by the LP3988-Q1.

The ceramic capacitor's capacitance can vary with temperature. Most large-value ceramic capacitors (\approx 2.2 μF) are manufactured with Z5U or Y5V temperature characteristics, which results in the capacitance dropping by more than 50% as the temperature goes from 25°C to 85°C.

A better choice for temperature coefficient in a ceramic capacitor is X7R, which holds the capacitance within \pm 15%.

Tantalum capacitors are less desirable than ceramic for use as output capacitors because they are more expensive when comparing equivalent capacitance and voltage ratings in the 1- μF to 4.7- μF range.

Another important consideration is that tantalum capacitors have higher ESR values than equivalent-size ceramics. This means that while it may be possible to find a tantalum capacitor with an ESR value within the stable range, it would have to be larger in capacitance (which means bigger and more costly) than a ceramic capacitor with the same ESR value. It should also be noted that the ESR of a typical tantalum will increase about 2:1 as the temperature goes from 25°C down to -40°C, so some guard band must be allowed.

9.2.2.6 Power Dissipation

Knowing the device power dissipation and proper sizing of the thermal plane connected to the tab or pad is critical to ensuring reliable operation. Device power dissipation depends on input voltage, output voltage, and load conditions and can be calculated with [Equation 1](#).

$$P_{D(MAX)} = (V_{IN(MAX)} - V_{OUT}) \times I_{OUT(MAX)} \quad (1)$$

Power dissipation can be minimized, and greater efficiency can be achieved, by using the lowest available voltage drop option that would still be greater than the dropout voltage (V_{DO}). However, keep in mind that higher voltage drops result in better dynamic (that is, PSRR and transient) performance.

On the SOT-23 (DBV) package, the primary conduction path for heat is through the device leads to the PCB, predominately device lead 2 (GND). TI recommends that the trace from lead 2 be extended under the package body and connected to an internal ground plane with thermal vias.

The maximum allowable junction temperature ($T_{J(MAX)}$) determines maximum power dissipation allowed ($P_{D(MAX)}$) for the device package.

Power dissipation and junction temperature are most often related by the junction-to-ambient thermal resistance ($R_{\theta JA}$) of the combined PCB and device package and the temperature of the ambient air (T_A), according to [Equation 2](#) or [Equation 3](#):

$$T_{J(MAX)} = T_{A(MAX)} + (R_{\theta JA} \times P_{D(MAX)}) \quad (2)$$

$$P_{D(MAX)} = (T_{J(MAX)} - T_{A(MAX)}) / R_{\theta JA} \quad (3)$$

Unfortunately, this $R_{\theta JA}$ is highly dependent on the heat-spreading capability of the particular PCB design, and therefore varies according to the total copper area, copper weight, and location of the planes. The $R_{\theta JA}$ recorded in [Thermal Information](#) is determined by the specific EIA/JEDEC JESD51-7 standard for PCB and copper-spreading area, and is to be used only as a relative measure of package thermal performance.

9.2.2.7 Estimating Junction Temperature

The EIA/JEDEC standard recommends the use of psi (Ψ) thermal characteristics to estimate the junction temperatures of surface mount devices on a typical PCB board application. These characteristics are not true thermal resistance values, but rather package specific thermal characteristics that offer practical and relative means of estimating junction temperatures. These psi metrics are determined to be significantly independent of copper-spreading area. The key thermal characteristics (Ψ_{JT} and Ψ_{JB}) are given in [Thermal Information](#) and are used in accordance with [Equation 4](#) or [Equation 5](#).

$$T_{J(MAX)} = T_{TOP} + (\Psi_{JT} \times P_{D(MAX)})$$

where

- $P_{D(MAX)}$ is explained in [Equation 1](#).
- T_{TOP} is the temperature measured at the center-top of the device package. (4)

$$T_{J(MAX)} = T_{BOARD} + (\Psi_{JB} \times P_{D(MAX)})$$

where

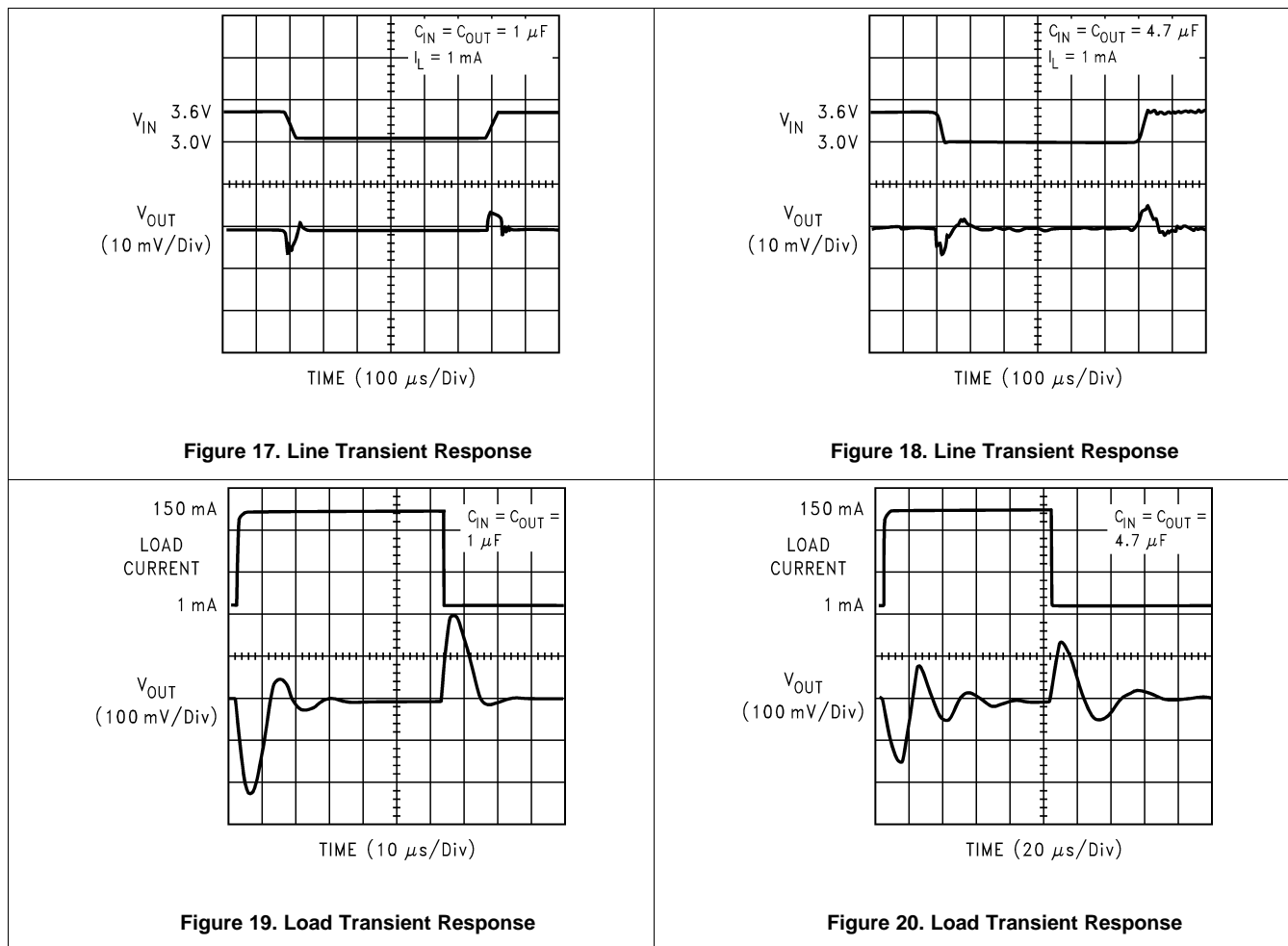
- $P_{D(MAX)}$ is explained in [Equation 1](#).
- T_{BOARD} is the PCB surface temperature measured 1-mm from the device package and centered on the package edge. (5)

For more information about the thermal characteristics Ψ_{JT} and Ψ_{JB} , see [Semiconductor and IC Package Thermal Metrics](#), available for download at www.ti.com.

For more information about measuring T_{TOP} and T_{BOARD} , see [Using New Thermal Metrics](#), available for download at www.ti.com.

For more information about the EIA/JEDEC JESD51 PCB used for validating $R_{\theta JA}$, see the [Thermal Characteristics of Linear and Logic Packages Using JEDEC PCB Designs](#), available for download at www.ti.com.

9.2.3 Application Curves



10 Power Supply Recommendations

The LP3988-Q1 device is designed to operate from an input supply voltage range of 2.5 V to 6 V. The input supply must be well regulated and free of spurious noise. To ensure that the LP3988-Q1 output voltage is well regulated and dynamic performance is optimum, the input supply voltage is recommended to be at least the greater of either $V_{OUT} + 200 \text{ mV}$, or 2.5 V.

11 Layout

11.1 Layout Guidelines

The dynamic performance of the LP3988-Q1 is dependant on the layout of the PCB. PCB layout practices that are adequate for typical LDOs may degrade the PSRR, noise, or transient performance of the LP3988-Q1.

Best performance is achieved by placing C_{IN} and C_{OUT} on the same side of the PCB as the LP3988-Q1 device, and as close as is practical to the package. The ground connections for C_{IN} and C_{OUT} must be back to the LP3988-Q1 GND pin using as wide and as short of a copper trace as is practical.

Avoid connections using long trace lengths, narrow trace widths, and/or connections through vias. These add parasitic inductances and resistance that results in inferior performance especially during transient conditions.

The PG pin pullup resistor must be connected to the LP3988-Q1 OUT pin, with the pullup resistor located as close as is practical to the PG pin.

11.2 Layout Example

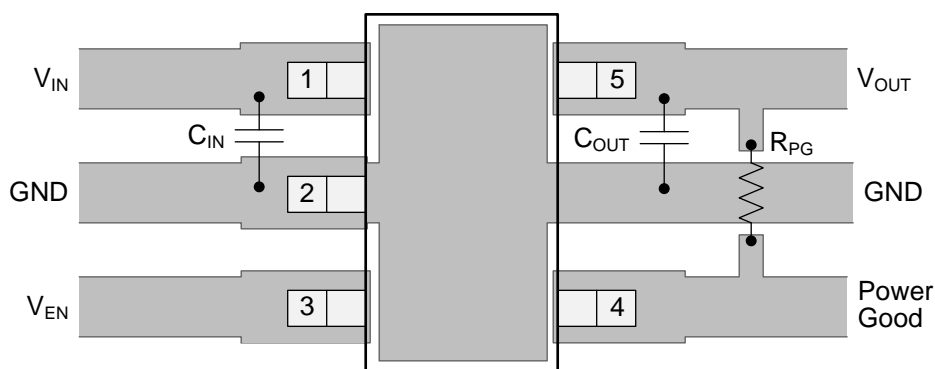


Figure 21. LP3988-Q1 SOT-23 Layout Example

12 Device And Documentation Support

12.1 Related Documentation

For additional information, see the following:

- [Semiconductor and IC Package Thermal Metrics](#)
- [Using New Thermal Metrics](#)
- [Thermal Characteristics of Linear and Logic Packages Using JEDEC PCB Designs](#)

12.2 Receiving Notification Of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, And Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LP3988QMFx-2P85	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	RABQ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF LP3988-Q1 :

- Catalog: [LP3988](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LP3988QMFx-2P85	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LP3988QMFx-2P85	SOT-23	DBV	5	3000	208.0	191.0	35.0

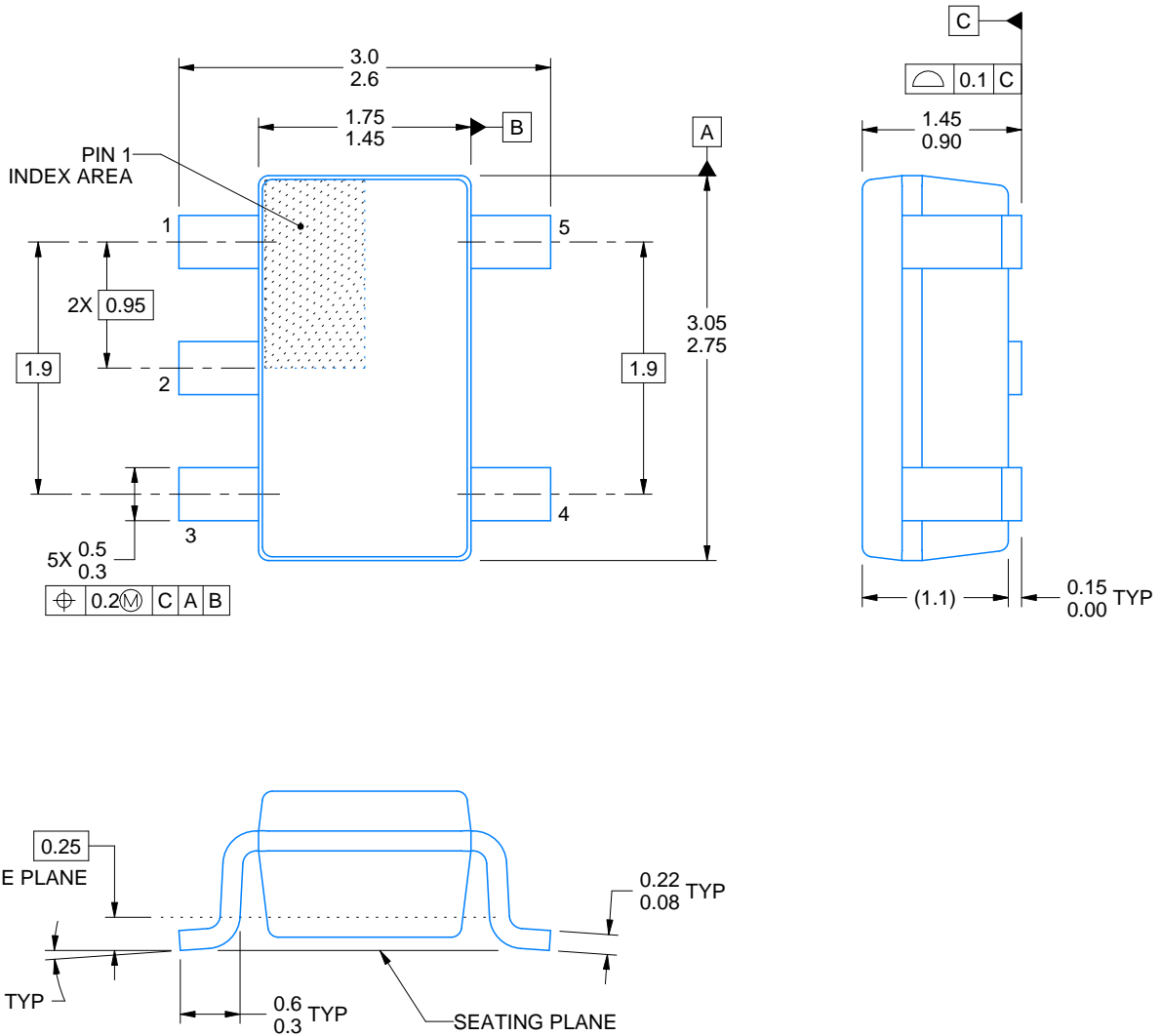


DBV0005A

PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



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NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.

EXAMPLE BOARD LAYOUT

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

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NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

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NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

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